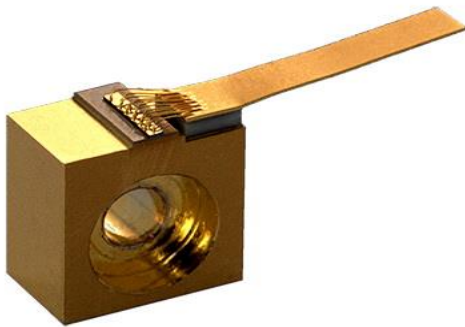


BA-1150-CM-4W
 High Power Broad-Area Laser Diode on Open Heatsink



Features:

- Output power 4W @ 1150nm in CW mode
- Proprietary mirror coating technology enabling high reliability
- Reliable Au/Sn bonding of chip to composite submount
- RoHS compliance

Applications:

- Medical Devices
- Sensors
- Scientific Research et al.

Recommended Operating Conditions
 Sample is mounted on a copper heatsink

Parameter	Min.	Typ.	Max.	Unit
Heatsink Temperature		25		°C
Forward Current		8	9.5	A
Output Power	0.4		4	W

Characteristics
 Tested for each sample @ CW, 25C, 8A

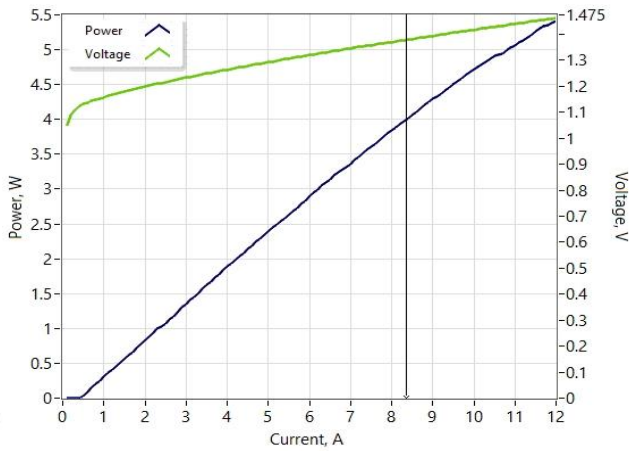
Parameter	Min.	Typ.	Max.	Unit
Output Power @ 9.5A	4			W
Forward Voltage		1.4	1.9	V
Threshold Current		0.4	0.8	A
Mean Wavelength	1140	1150	1160	nm
Bandwidth (FWHM)		10	15	nm
Wavelength Temperature Tunability		0.5		nm/°C
Slow Axis Beam Divergence (FWHM)	4	8	12	deg
Fast Axis Beam Divergence (FWHM)		40	45	deg
Mesa Width		90		µm
Polarization		TE		

Absolute Maximum Ratings

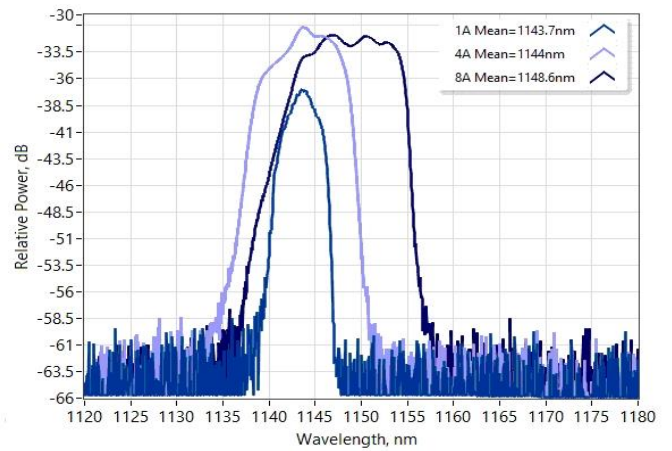
Parameter	Min	Max	Unit
Forward Current (CW)		10	A
Reverse Voltage		2	V
Soldering Temperature (5 sec. max)		250	°C
Operating temperature (above dew point)	5	60	°C
Storage Temperature	-40	85	°C

Typical Performance (for reference only)

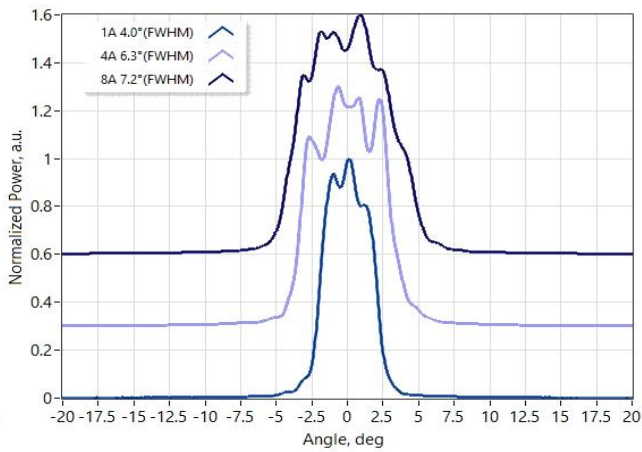
Light-Current-Voltage Characteristics



Optical Spectra (res. 1nm)



Slow Axis Far Field



Fast Axis Far Field

